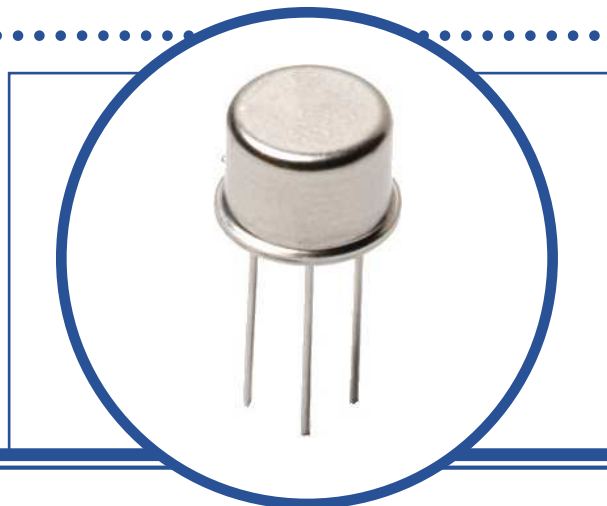


# N-CHANNEL ENHANCEMENT MODE MOSFET 2N6659X

- Switching Regulators
- Converters
- Motor Drives



## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise stated)

$V_{DS}$	Drain – Source Voltage		35V
$V_{GS}$	Gate – Source Voltage		$\pm 20\text{V}$
$I_D$	Drain Current	$T_C = 25^\circ\text{C}$	1.4A
$I_D$	Drain Current	$T_C = 100^\circ\text{C}$	1.0A
$I_{DM}^1$	Pulsed Drain Current		3A
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	6.25W
		Derate Above $T_C = 25^\circ\text{C}$	0.05W/ $^\circ\text{C}$
$T_J$	Junction Temperature Range		-55 to +150 $^\circ\text{C}$
$T_{stg}$	Storage Temperature Range		-55 to +150 $^\circ\text{C}$

<sup>1</sup> Pulse width limited by maximum junction temperature.

# N-CHANNEL ENHANCEMENT MODE MOSFET 2N6659X

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
$V_{(BR)DSS}$	Drain – Source Breakdown Voltage	$V_{GS} = 0$ $I_D = 10\mu\text{A}$	35			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 1.0\text{mA}$	0.8	1.6	2	
$I_{GSS}$	Gate – Body Leakage Current	$V_{GS} = \pm 15\text{V}$ $V_{DS} = 0\text{V}$ $T_C = 125^\circ\text{C}$			$\pm 100$ $\pm 500$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 35\text{V}$ $V_{GS} = 0$ $V_{DS} = 35\text{V}$ $V_{GS} = 0$ $T_C = 125^\circ\text{C}$			10 500	$\mu\text{A}$
$I_{D(on)^2}$	On-State Drain Current	$V_{DS} = 15\text{V}$ $V_{GS} = 10\text{V}$	1.5	1.8		A
$R_{DS(on)^2}$	Drain – Source On Resistance	$V_{GS} = 5\text{V}$ $I_D = 0.3\text{A}$ $V_{GS} = 10\text{V}$ $I_D = 1.0\text{A}$		1.8 1.3	5 2	$\Omega$
$V_{DS(on)^2}$	Drain – Source On Voltage	$V_{GS} = 5\text{V}$ $I_D = 0.3\text{A}$ $V_{GS} = 10\text{V}$ $I_D = 1.0\text{A}$		0.54 1.3	1.5 2	V

## DYNAMIC CHARACTERISTICS

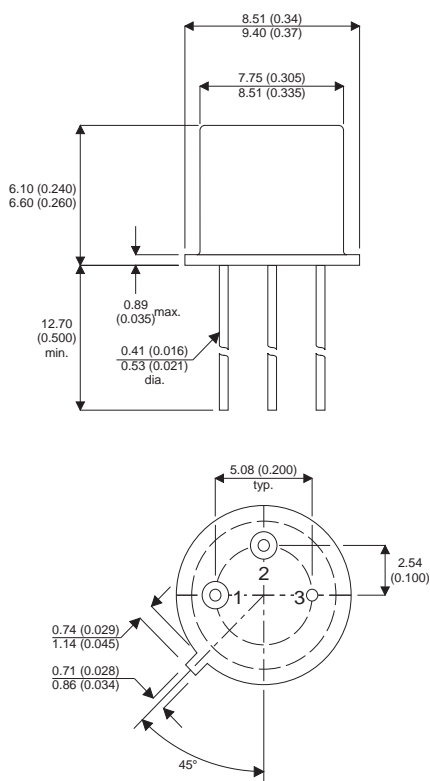
$R_{DS(on)}$	Small Signal Drain – Source On Resistance	$V_{GS} = 10\text{V}$ $I_D = 1.0\text{A}$ $f = 1.0\text{KHz}$		1.3	2	$\Omega$
$t_{off}$	Turn-On Time	$V_{DD} = 25\text{V}$ $V_{GEN} = 10\text{V}$ $R_L = 23\Omega$ $R_G = 25\Omega$ $I_D = 1.0\text{A}$		8	10	ns
$t_{on}$	Turn-Off Time			9	10	
$g_{FS}^2$	Forward Transconductance	$V_{DS} = 10\text{V}$ $I_D = 0.5\text{A}$	170	350		ms
$C_{iss}$	Input Capacitance	$V_{DS} = 24\text{V}$ $V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$		35	50	pF
$C_{oss}$	Output Capacitance			28	40	
$C_{rss}$	Reverse Transfer Capacitance			2	10	

<sup>2</sup> Pulse Test  $t_p \leq 380 \mu\text{s}$ ,  $\delta \geq 2\%$

# N-CHANNEL ENHANCEMENT MODE MOSFET 2N6659X

## MECHANICAL DATA

Dimensions in mm (inches)



## TO-39 (TO-205AD) METAL PACKAGE

**PIN1 – SOURCE**

**PIN2 – GATE**

**PIN3/CASE – DRAIN**